OPA8831

Infrared LED Chip

High Speed / N Side-Up

GaAlAs/GaAlAs

1. Material

Substrate GaAlAs (P Type) Removed
Epitaxial Layer GaAlAs (N/P Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

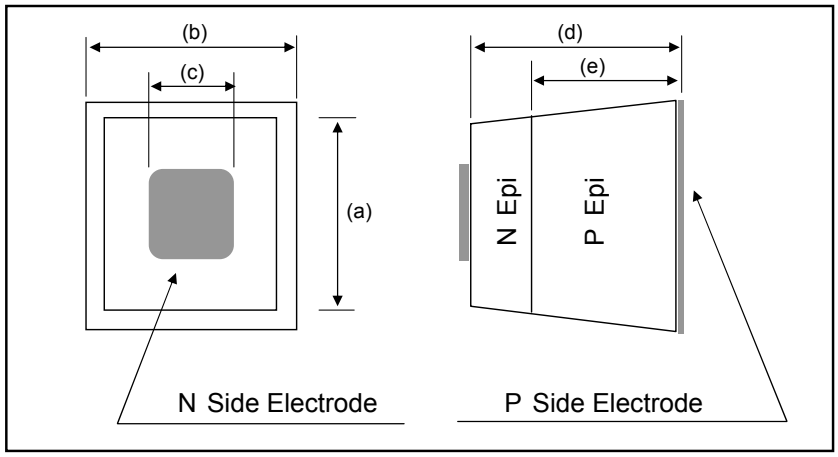
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$		1.8	2	V	IF=100mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O	10	12		mW	IF=100mA
Wavelength	λ_P		880		nm	IF=20mA
	$\Delta\lambda$		80		nm	IF=20mA
Rise Time	Tr		700		ns	
Fall Time	Tf		400		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area ---------- 11.6mil x 11.6mil
(b) Bottom Area ---------- 12.6mil x 12.6mil
(c) Bonding Pad ---------- 130um
(d) Chip Thickness ---------- 10mil
(e) Junction Height ---------- 9.0mil



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